

4V Drive Pch MOSFET

RSM002P03

●Structure

Silicon P-channel MOSFET

●Features

- 1) Low On-resistance.
- 2) Small package (VMT3).
- 3) 4V drive.

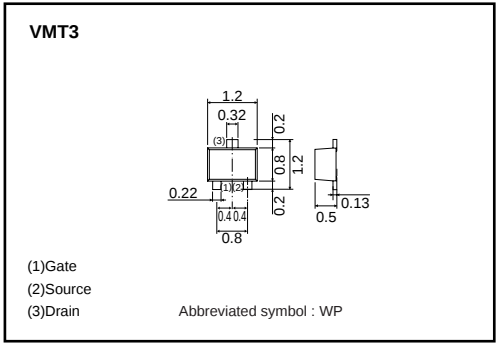
●Applications

Switching

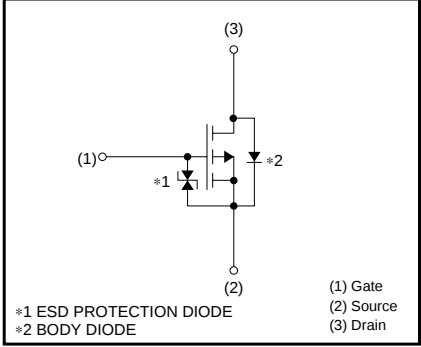
●Packaging specifications

Type	Package	Taping
	Code	T2L
	Basic ordering unit (pieces)	8000
RSM002P03		○

●Dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	-30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±0.2	A
	Pulsed	I_{DP} *1	±0.4	A
Total power dissipation		P_D *2	0.15	W
Channel temperature		T_{ch}	150	°C
Range of storage temperature		T_{stg}	-55 to +150	°C

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

*2 Each terminal mounted on a recommended land

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th(ch-a)}$ *	833	°C/W

* Each terminal mounted on a recommended land

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR) DSS}$	−30	—	—	V	$I_D = -1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	—	—	−1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	−1.0	—	−2.5	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	—	0.9	1.4	Ω	$I_D = -0.2A, V_{GS} = -10V$
		—	1.4	2.1	Ω	$I_D = -0.15A, V_{GS} = -4.5V$
		—	1.6	2.4	Ω	$I_D = -0.15A, V_{GS} = -4.0V$
Forward transfer admittance	$ Y_{fs} ^*$	0.2	—	—	S	$V_{DS} = -10V, I_D = -0.15A$
Input capacitance	C_{iss}	—	30	—	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	—	4	—	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	—	5	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	—	8	—	ns	$V_{DD} = -15V$
Rise time	t_r^*	—	5	—	ns	$I_D = -0.15A$
Turn-off delay time	$t_{d(off)}^*$	—	30	—	ns	$V_{GS} = -10V$
Fall time	t_f^*	—	40	—	ns	$R_L = 100\Omega$ $R_G = 10\Omega$

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	—	—	−1.2	V	$I_S = -0.1A, V_{GS} = 0V$

Transistors

●Electrical characteristics curves

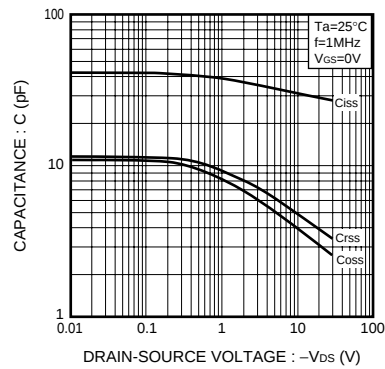


Fig.1 Typical Capacitance vs. Drain-Source Voltage

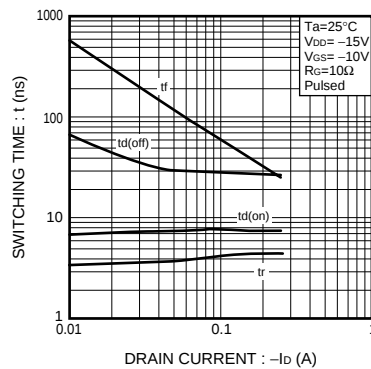


Fig.2 Switching Characteristics

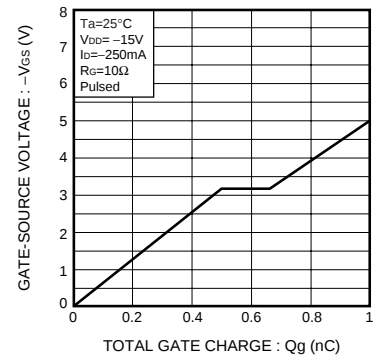


Fig.3 Dynamic Input Characteristics

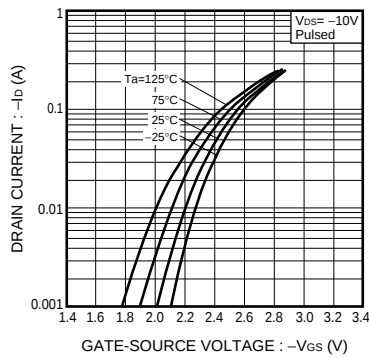


Fig.4 Typical Transfer Characteristics

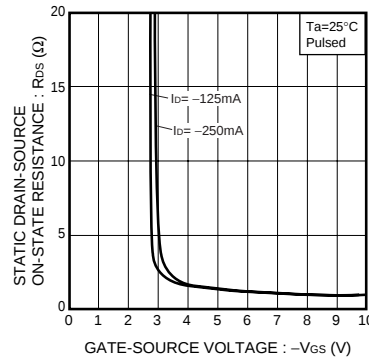


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

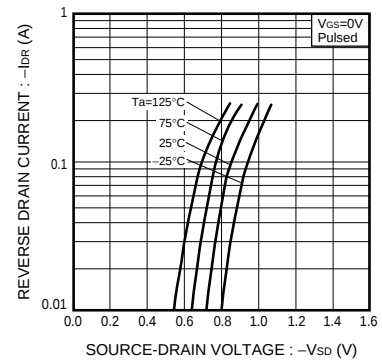


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

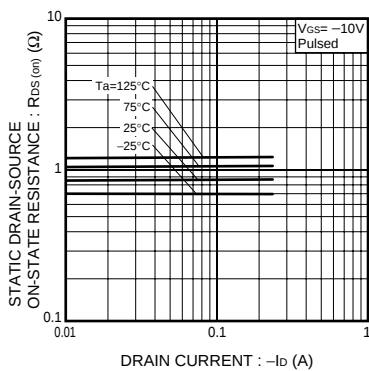


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

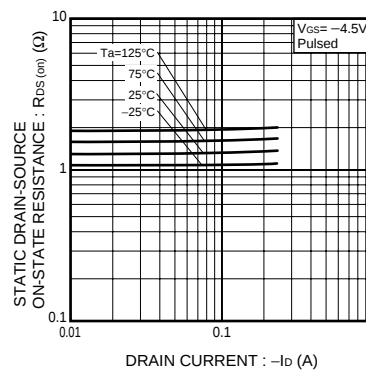


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

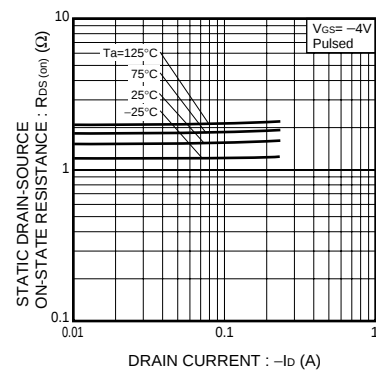


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

Transistors

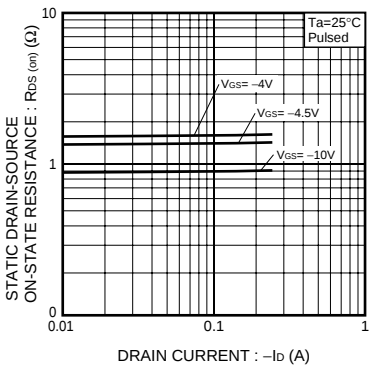


Fig.10 Static Drain-Source
On-State Resistance
vs. Drain Current (IV)

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